







#### **DUAL 12V PNP LOW SATURATION TRANSISTORS**

#### **Features and Benefits**

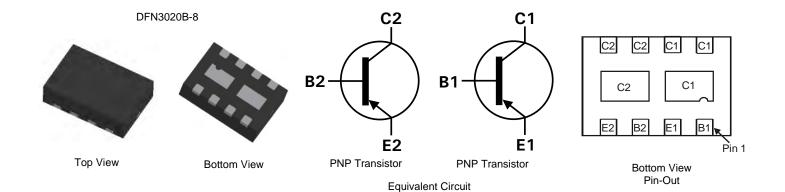
- BV<sub>CEO</sub> > -12V
- I<sub>C</sub> = -4A Continuous Collector Current
- Low Saturation Voltage (-140mV @ -1A)
- R<sub>SAT</sub> = 60 mΩ for a low equivalent On-Resistance
- h<sub>FE</sub> specified up to -10A for a high current gain hold up
- Dual NPN saving footprint and component count
- Low profile 0.8mm high package for thin applications
- R<sub>0,JA</sub> efficient, 40% lower than SOT26
- 6mm<sup>2</sup> footprint, 50% smaller than TSOP6 and SOT26
- Lead-Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: DFN3020B-8
- Case material: Molded Plastic. "Green" Molding Compound.
- Terminals: Pre-Plated NiPdAu leadframe.
- Nominal package height: 0.8mm
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.013 grams (approximate)

### **Applications**

- DC-DC Converters
- Charging circuits
- Power switches
- Motor drive



### **Ordering Information**

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTD717MCTA	D11	7	8	3000

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

## **Marking Information**



D11 = Product type marking code Top view, dot denotes pin 1





### **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit	
Collector-Base Voltage		$V_{CBO}$	-20		
Collector-Emitter Voltage		$V_{CEO}$	-12	V	
Emitter-Base Voltage		V <sub>EBO</sub>	-7		
Peak Pulse Current		I <sub>CM</sub>	-12		
Continuous Collector Current	(Notes 3 & 6)	I-	-4	] ,	
	(Notes 4 & 6)	IC	-4.4	A	
Base Current		Ι <sub>Β</sub>	1		

## Thermal Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
	(Notes 3 & 6)		1.5 12	
Power Dissipation	(Notes 4 & 6)		2.45 19.6	W
Linear Derating Factor	(Notes 5 & 6)	P <sub>D</sub>	1.13 8	mW/°C
	(Notes 5 & 7)		1.7 13.6	
	(Notes 3 & 6)		83.3	
Thermal Desigtance Junction to Ambient	(Notes 4 & 6)		51.0	
Thermal Resistance, Junction to Ambient	(Notes 5 & 6)	$R_{\theta JA}$	111	°C/W
	(Notes 5 & 7)		73.5	
Thermal Resistance, Junction to Lead (Notes 6 & 8)		$R_{ heta JL}$	17.1	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

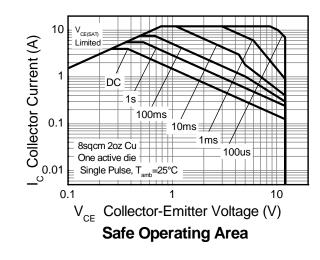
#### Notes:

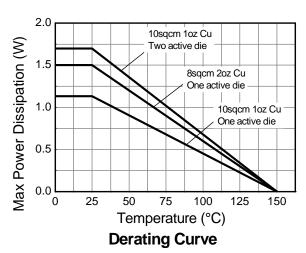
- 3. For a dual device surface mounted on 28mm x 28mm (8cm²) FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The heatsink is split in half with the exposed collector pads connected to each half.
- 4. Same as note (3), except the device is measured at t <5 sec.
- 5. Same as note (3), except the device is surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper.
- 6. For a dual device with one active die.
- 7. For dual device with 2 active die running at equal power.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).

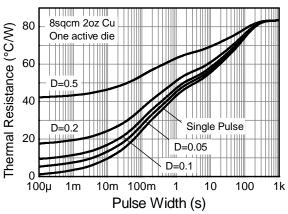


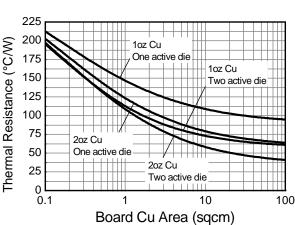


#### **Thermal Characteristics**



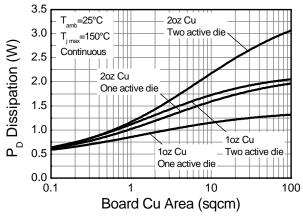






### **Transient Thermal Impedance**

Thermal Resistance v Board Area



**Power Dissipation v Board Area** 





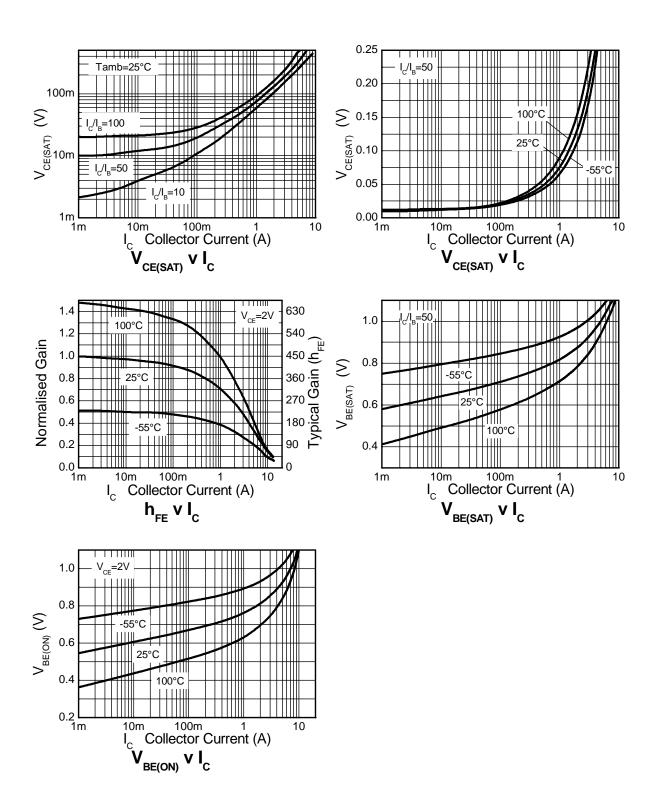
# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	-20	-35	-	٧	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-12	-25	-	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-7	-8.5	-	V	$I_E = -100 \mu A$
Collector Cutoff Current	I <sub>CBO</sub>	-	-	-100	nA	V <sub>CB</sub> = -16V
Emitter Cutoff Current	I <sub>EBO</sub>	-	-	-100	. nA	$V_{EB} = -6V$
Collector Emitter Cutoff Current	I <sub>CES</sub>	-	-	-100	nA	V <sub>CES</sub> = -10V
		300	475	-	-	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -2V
		300	450	-	-	$I_C = -100 \text{mA}, V_{CE} = -2 \text{V}$
Static Forward Current Transfer Ratio (Note 9)	h <sub>FE</sub>	180	275	-	-	$I_C = -2.5A$ , $V_{CE} = -2V$
		60	100	-	-	$I_C = -8A$ , $V_{CE} = -2V$
		45	70	-	-	$I_C = -10A$ , $V_{CE} = -2V$
		-	-10	-17	mV	$I_C = -0.1A$ , $I_B = -10mA$
	V <sub>CE(sat)</sub>	-	-100	-140	mV	$I_C = -1A, I_B = -10mA$
Collector-Emitter Saturation Voltage (Note 9)		-	-100	-150	mV	$I_C = -1.5A$ , $I_B = -50mA$
		-	-195	-300	mV	$I_C = -3A$ , $I_B = -50mA$
		-	-240	-310	mV	$I_C = -4A$ , $I_B = -150mA$
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(on)</sub>	-	-0.87	-0.96	V	$I_C = -4A$ , $V_{CE} = -2V$
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	-	-0.97	-1.07	V	$I_{C}$ = -4A, $I_{B}$ = -150mA
Output Capacitance	C <sub>obo</sub>	-	21	30	pF	V <sub>CB</sub> = -10V. f = 1MHz
Transition Frequency	f <sub>T</sub>	100	110	-	MHz	V <sub>CE</sub> = -10V, I <sub>C</sub> = -50mA, f = 100MHz
Turn-on Time	t <sub>on</sub>	-	70	-	ns	$V_{CC} = -6V$ , $I_C = -2A$
Turn-off Time	t <sub>off</sub>	-	130	-	ns	$I_{B1} = I_{B2} = -50 \text{mA}$

Notes: 9. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu$ s. Duty cycle  $\leq$  2%



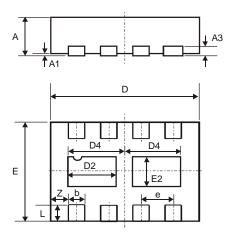
# **Typical Electrical Characteristics**





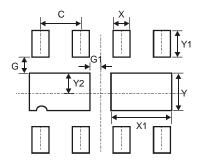


# **Package Outline Dimensions**



DFN3020B-8					
Dim	Min	Max	Тур		
Α	0.77	0.83	0.80		
A1	0	0.05	0.02		
A3	-	-	0.15		
b	0.25	0.35	0.30		
D	2.95	3.075	3.00		
D2	0.82	1.02	0.92		
D4	1.01	1.21	1.11		
е	-	-	0.65		
Е	1.95	2.075	2.00		
E2	0.43	0.63	0.53		
L	0.25	0.35	0.30		
Z	-	-	0.375		
All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)
С	0.650
G	0.285
G1	0.090
Х	0.400
X1	1.120
Y	0.730
Y1	0.500
Y2	0.365





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